INTEGRATED CIRCUITS

DATA SHEET

74F308-input NAND gate

Product specification

1989 Mar 03

IC15 Data Handbook





8-input NAND gate

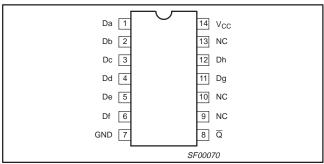
74F30

TYPE	TYPICAL PROPAGATION DELAY	TYPICAL SUPPLY CURRENT (TOTAL)
74F30	3.2ns	1.7mA

ORDERING INFORMATION

DESCRIPTION	COMMERCIAL RANGE V_{CC} = 5V $\pm 10\%$, T_{amb} = 0°C to +70°C	PKG DWG #
14-pin plastic DIP	N74F30N	SOT27-1
14-pin plastic SO	N74F30D	SOT108-1

PIN CONFIGURATION

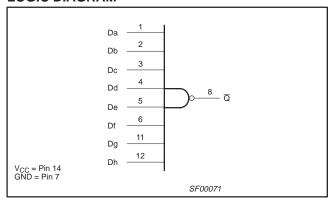


INPUT AND OUTPUT LOADING AND FAN OUT TABLE

PINS	DESCRIPTION	74F (U.L.) HIGH/LOW	LOAD VALUE HIGH/LOW
Dn	Data inputs	1.0/1.0	20μA/0.6mA
Q	Data output	50/33	1.0mA/20mA

NOTE: One (1.0) FAST unit load is defined as: 20μA in the High state and 0.6mA in the Low state.

LOGIC DIAGRAM



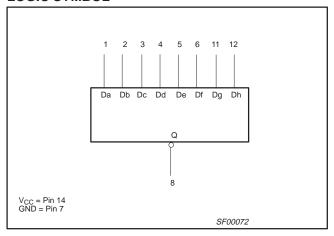
FUNCTION TABLE

			INP	UTS				OUTPUT
Dna	Dnb	Dnc	Dnd	Dne	Dnf	Dng	Dnh	Qn
L	Х	Χ	Х	X X		Х	Χ	Н
X	L	Χ	Χ	Χ	Χ	Χ	Χ	Н
Х	Χ	L	Χ	Χ	X	Χ	Χ	н
Х	Χ	Χ	L	Χ	Χ	Χ	Χ	Н
Х	Χ	Χ	Χ	L	Χ	Χ	Х	Н
X	Χ	Χ	Χ	Χ	L	Χ	Χ	Н
X	X	Χ	Χ	Χ	X	L	Χ	Н
Х	Χ	Χ	Χ	Χ	Χ	Χ	L	Н
Н	Н	Н	Н	Н	Н	Н	Н	Ĺ

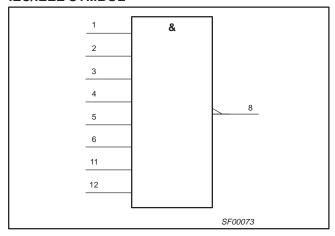
NOTES:

- 1. H = High voltage level
- 2. L = Low voltage level
- 3. X = Don't care

LOGIC SYMBOL



IEC/IEEE SYMBOL



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ABSOLUTE MAXIMUM RATINGS

(Operation beyond the limit set forth in this table may impair the useful life of the device. Unless otherwise noted these limits are over the operating free-air temperature range.)

SYMBOL	PARAMETER	RATING	UNIT
V _{CC}	Supply voltage	-0.5 to +7.0	V
V _{IN}	Input voltage	-0.5 to +7.0	V
I _{IN}	Input current	−30 to +5	mA
V _{OUT}	Voltage applied to output in High output state	–0.5 to V _{CC}	V
I _{OUT}	Current applied to output in Low output state	40	mA
T _{amb}	Operating free-air temperature range	0 to +70	°C
T _{stg}	Storage temperature range	-65 to +150	°C

RECOMMENDED OPERATING CONDITIONS

CVMDOL	DADAMETED	LIMITS							
SYMBOL	PARAMETER	MIN	NOM	MAX	UNIT				
V _{CC}	Supply voltage	4.5	5.0	5.5	V				
V_{IH}	High-level input voltage	2.0			V				
V _{IL}	Low-level input voltage			0.8	V				
I _{IK}	Input clamp current			-18	mA				
I _{OH}	High-level output current			-1	mA				
I _{OL}	Low-level output current			20	mA				
T _{amb}	Operating free-air temperature range	0		+70	°C				

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DC ELECTRICAL CHARACTERISTICS

(Over recommended operating free-air temperature range unless otherwise noted.)

OVMDOL	DADAMETER		TEGT CONDITIO	NO1		LIMITS		LIAUT
SYMBOL	PARAMETER		TEST CONDITIO	MIN	TYP ²	MAX	UNIT	
\ <u></u>	Light level output valte as		$V_{CC} = MIN, V_{IL} = MAX$	2.5			V	
V _{OH}	High-level output voltage		$V_{IH} = MIN, I_{OH} = MAX$	2.7	3.4		V	
V	Low lovel output voltage		$V_{CC} = MIN, V_{IL} = MAX$	$_{CC} = MIN, V_{IL} = MAX$ $\pm 10\% V_{CC}$			0.50	V
V _{OL}	Low-level output voltage		$V_{IH} = MIN, I_{OL} = MAX$		0.30	0.50	V	
V _{IK}	Input clamp voltage		$V_{CC} = MIN, I_I = I_{IK}$			-0.73	-1.2	V
I _I	Input current at maximum input volta	ige	$V_{CC} = MAX, V_I = 7.0V$			100	μΑ	
I _{IH}	High-level input current		$V_{CC} = MAX, V_I = 2.7V$				20	μΑ
I _{IL}	Low-level input current		$V_{CC} = MAX, V_I = 0.5V$				-0.6	mA
Ios	Short-circuit output current ³		$V_{CC} = MAX$		-60		-150	mA
1	Supply current (total)	I _{CCH}	V _{CC} = MAX	V _{IN} = GND		0.6	1.5	mA
Icc	Supply current (total)		ACC = INIVX	V _{IN} = 4.5V		2.8	4.0	IIIA

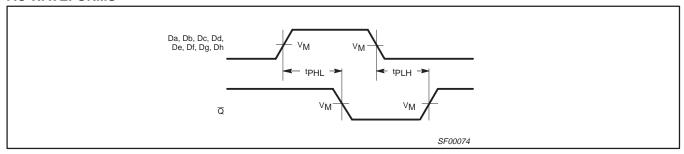
NOTES:

- 1. For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions for the applicable type.
- 2. All typical values are at $V_{CC} = 5V$, $T_{amb} = 25^{\circ}C$.
- 3. Not more than one output should be shorted at a time. For testing I_{OS}, the use of high-speed test apparatus and/or sample-and-hold techniques are preferable in order to minimize internal heating and more accurately reflect operational values. Otherwise, prolonged shorting of a High output may raise the chip temperature well above normal and thereby cause invalid readings in other parameter tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

AC ELECTRICAL CHARACTERISTICS

			LIMITS							
SYMBOL	PARAMETER	TEST CONDITION	Ta	C _C = +5.0 m _b = +25° 50pF, R _L =	C	$V_{CC} = +5.$ $T_{amb} = 0^{\circ}C$ $C_{L} = 50pF$	UNIT			
			MIN	TYP	MAX	MIN	MAX			
t _{PLH} t _{PHL}	Propagation delay Da, Db, Dc, Dd, De, Df, Dg, Dh to $\overline{\mathbb{Q}}$	Waveform 1	1.5 1.0	3.5 3.0	5.0 4.5	1.5 1.0	5.5 5.0	ns		

AC WAVEFORMS



Waveform 1. Propagation Delay for Inverting Outputs

NOTE:

For all waveforms, $V_M = 1.5V$.

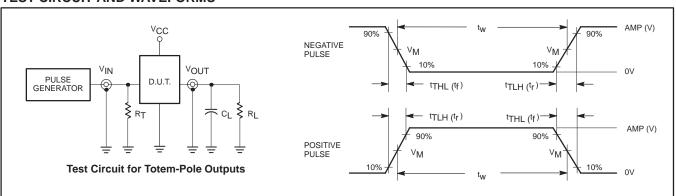
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TEST CIRCUIT AND WAVEFORMS



DEFINITIONS:

R_L = Load resistor; see AC ELECTRICAL CHARACTERISTICS for value.

 $C_L = Load$ capacitance includes jig and probe capacitance; see AC ELECTRICAL CHARACTERISTICS for value.

Termination resistance should be equal to Z_{OUT} of pulse generators.

Input Pulse Definition

family	INP	INPUT PULSE REQUIREMENTS											
	amplitude	V_{M}	rep. rate	t _w	t _{THL}								
74F	3.0V	1.5V	1.5V 1MHz		2.5ns	2.5ns							

SF00006

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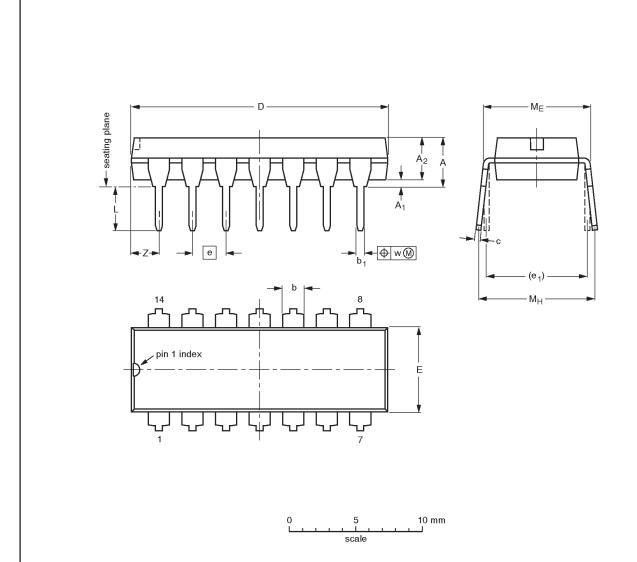
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DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	С	D ⁽¹⁾	E ⁽¹⁾	е	e ₁	L	ME	Мн	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.020	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	RENCES	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE		
SOT27-1	050G04	MO-001AA			92-11-17 95-03-11		

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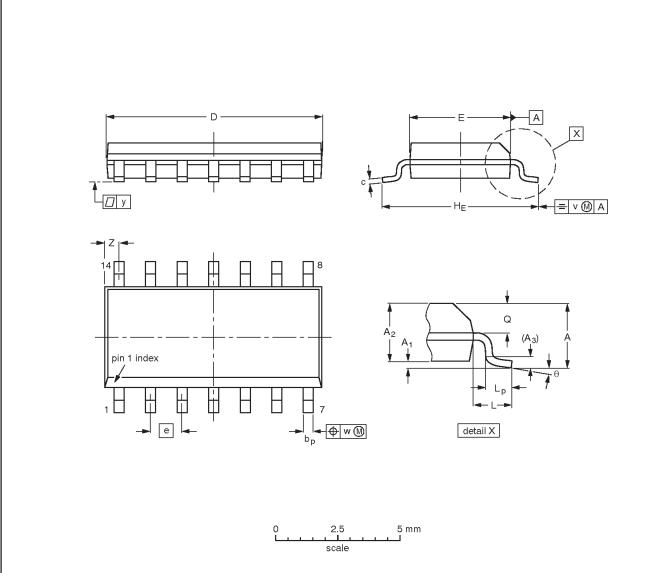
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SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	А3	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075	0.35 0.34	0.16 0.15	0.050	0.244 0.228	0.041	0.039 0.016		0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE
SOT108-1	076E06S	MS-012AB			95-01-23 97-05-22

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Data sheet status

Data sheet status	Product status	Definition [1]
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make chages at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

^[1] Please consult the most recently issued datasheet before initiating or completing a design.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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